Electrical Characteristics (@ T_C = 25℃ unless otherwise specified)

Parameter	Conditions	Symbol	Values			Unit
			Min.	Typ.	Max.	
Peak forward voltage	I_T=360A, t_P=380μs	V_T			1.80	V
Repetitive peak off-state current	V_D = V_{DRM},T_{vj} = 25	I_{DRM}			100	μA
	V_D = V_{DRM},T_{vj} = 125				40	mA
Reverse leakage current	V_R = V_{RRM},T_{vj} = 25	I_{RRM}			100	μA
	V_R = V_{RRM},T_{vj} = 125				40	mA
Threshold voltage	For power loss calculation only T_{vj} = 125 ,	V_{TO}			0.95	V
Dynamic resistance	T_{vj} = 125 ,	r_T			2.1	mΩ
Triggering gate current	V_D=12V R_L=30Ω	I_{GT}	20		120	mA
Holding current	I_T=1A	I_H			250	mA
Latching current	I_G=1.2 I_{GT}	I_L			300	mA
Critical rate of rise of voltage	V_D=2/3V_{DRM} Tvj=125 - Gate Open	dv/dt	1000			V/μs
Triggering gate voltage	V_D=12V R_L=30Ω	V_{GT}			1.8	V
Non triggering gate voltage	V_D=V_{DRM} Tvj=125	V_{GD}	0.25			V

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Ordering Information

Device	Marking	Package	Weight	Inner Box	Per Carton
JMT180KQ18V1C	JMT180KQ18V1C	V1	42.9g/PCS	60 PCS	360 PCS

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Circuit Diagram

Package Outlines (mm)

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